

# Statistical Analysis of Droplet Epitaxial Nano-structure Growth Parameters – as Preliminary for Technological Support

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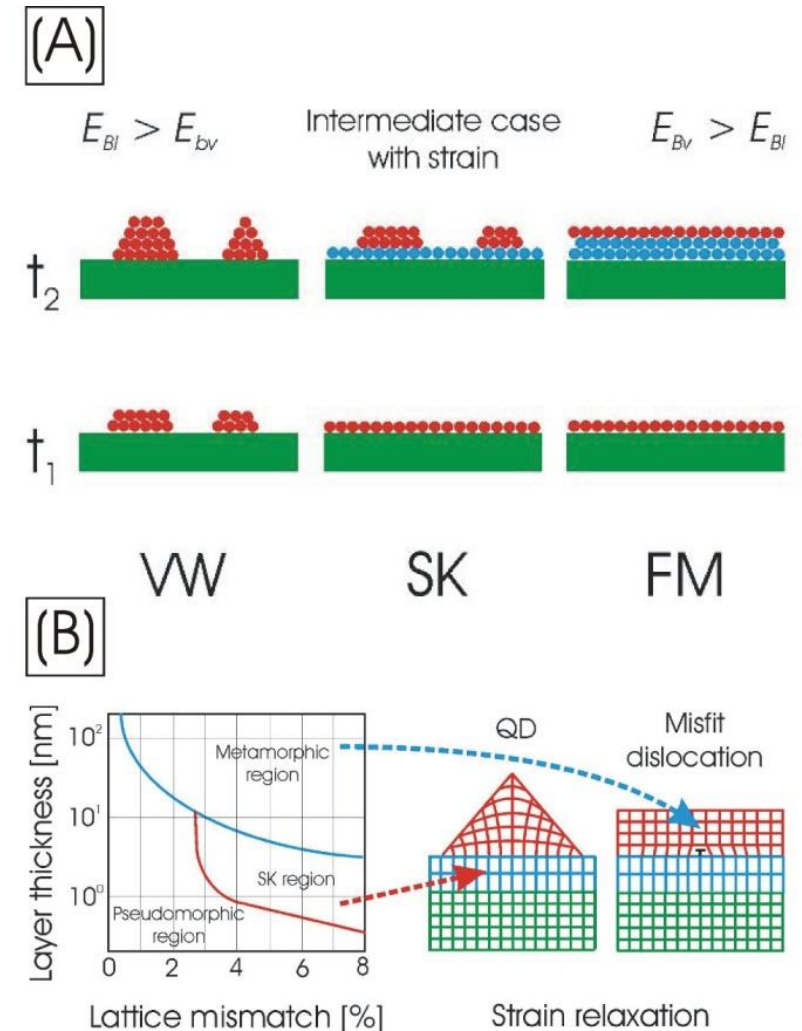
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# Why are nanostructures important?

- Generally application of nanostructures improves the yield of fabricating electronic devices
  - E.g. Improving efficiency of solar cells
  - E.g. improving LED emission
- Novel devices
  - Cellular automate
  - Advances in the field of computer parts (processors, memories, etc)
  - Optoelectronics
  - Quantumcomputation

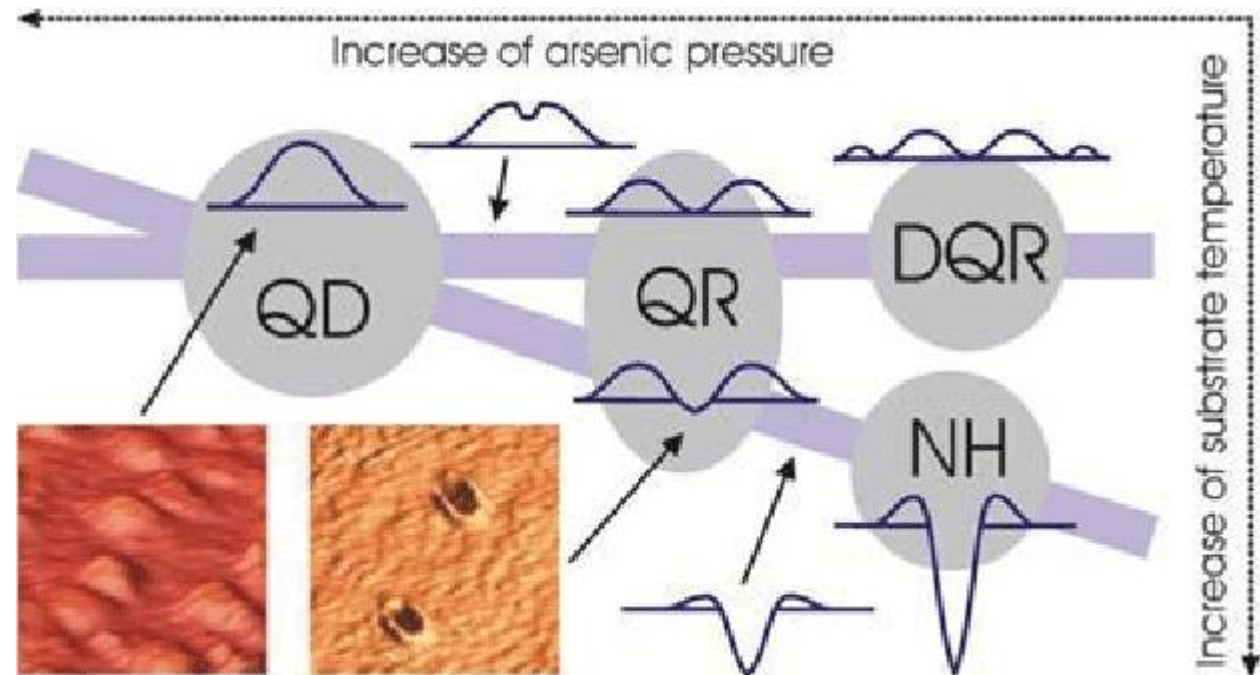
# Fabrication of nanostructures

- Strain induced epitaxial process
  - Limited range of shapes
  - Limited sortiment of materials
  - Limited distribution homogeneity
- Droplet epitaxial process
  - Wide range of shapes
  - Large sortiment of materials
  - Wide range of surficial density



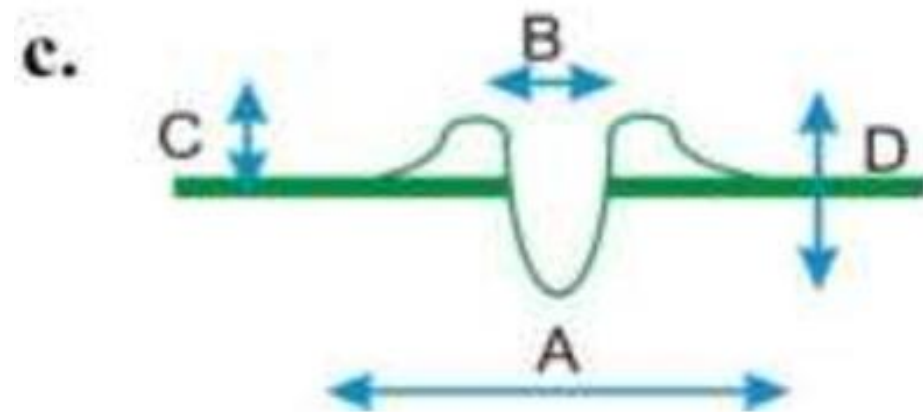
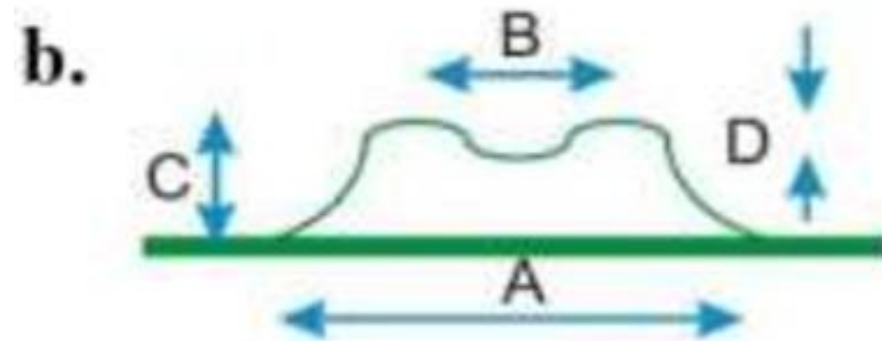
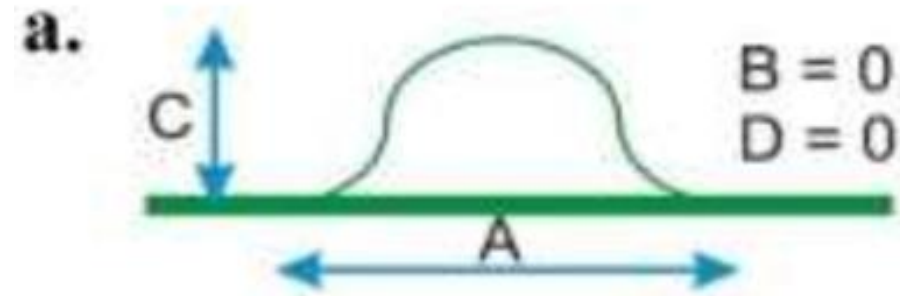
# Types of droplet epitaxial nanostructures

- Quantum Dots (QDs)
- Quantum Rings (QRs)
- Nanoholes (NHs)



# Dimensions of droplet-epitaxial nanostructures

- a) conventional shaped quantum dot (QD)
- b) cross section of nano-sized quantum ring (QR)
- c) cross section of a nano-hole, where the thick green line represents the substrate surface (NH)



# Looking for the connection between technological and geometrical parameters I.

## Linear approximation

- Simple linear regression (setting up and testing linear relationship between any two variables)
- Multiple linear regression (technological parameters as independent variables, surficial density and geometric parameters as dependent variables)

# Looking for the connection between technological and geometrical parameters II.

- Principal Component Analysis

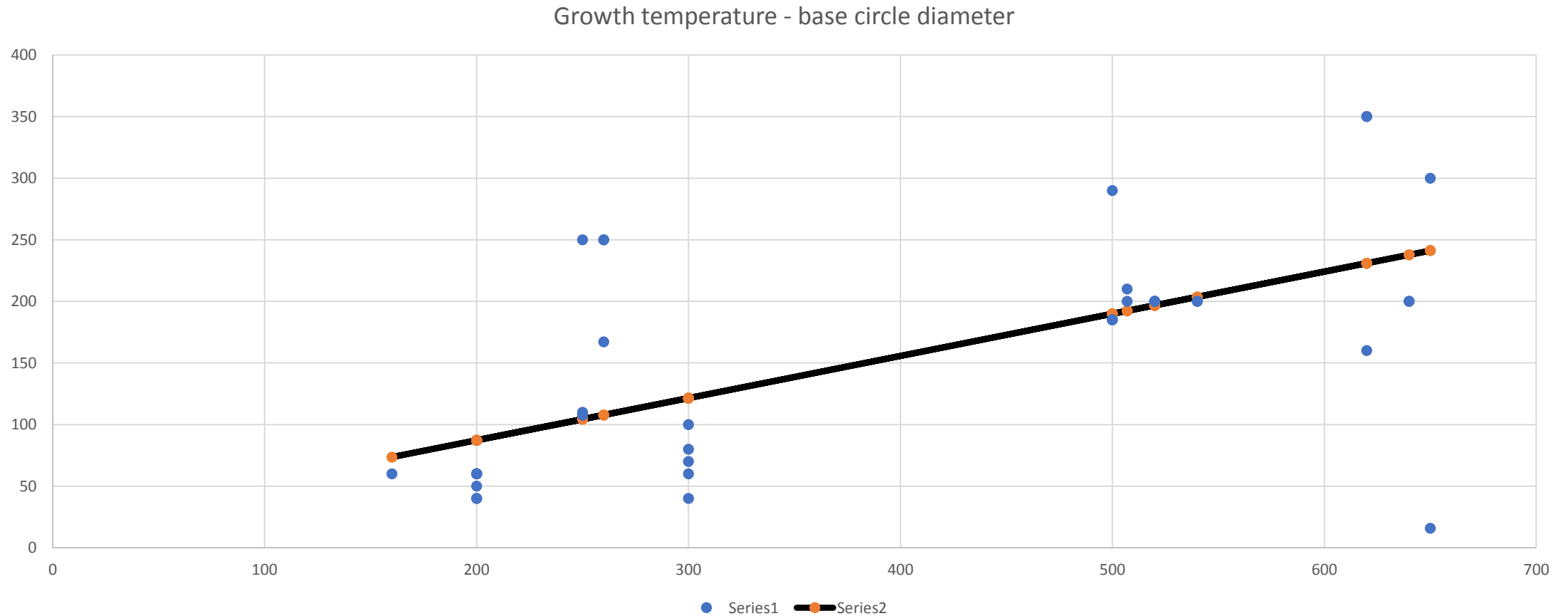
Returns as many pairwise orthogonal vectors as the dimension of data set; the first vector points to the direction of maximal variance; the second vector points to the direction of maximal variance still available AND orthogonal to the first vector and so on;

PCA can be used to reduce the number of dimensions of data set at the expense of minimal loss of information

- Soft computing methods (neural networks etc)

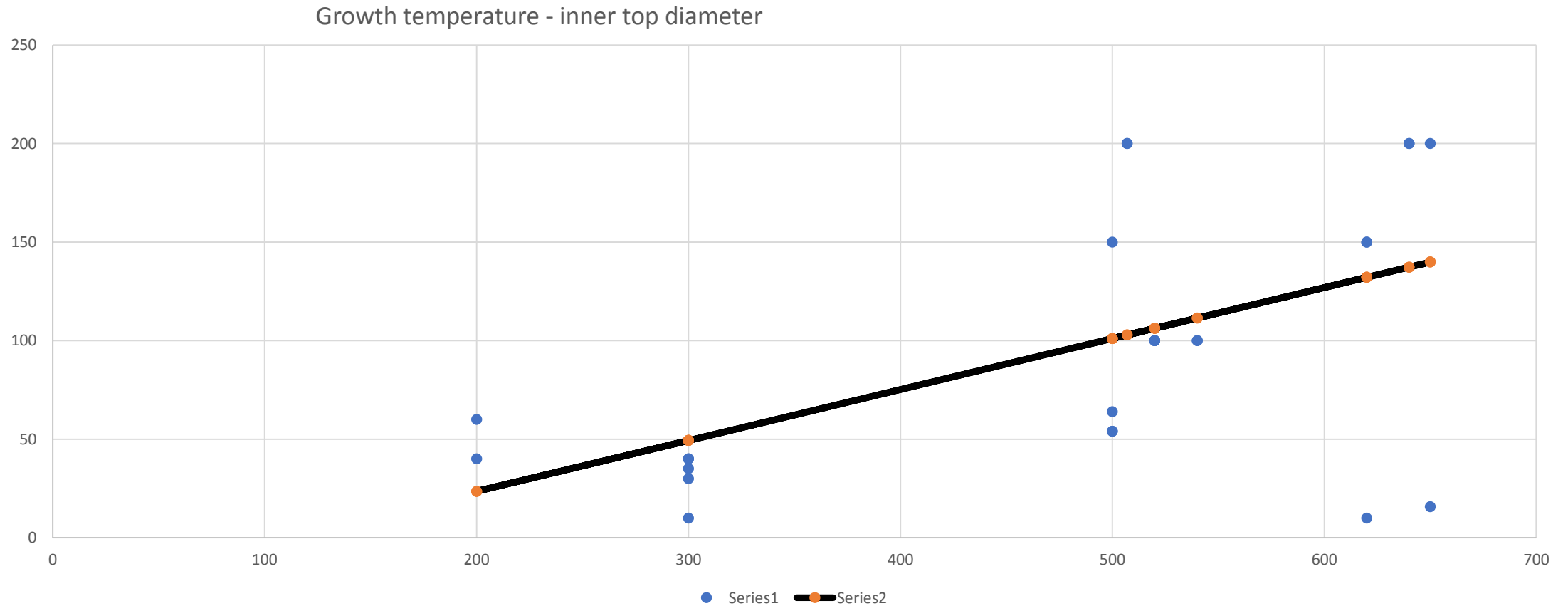
Unfortunately our present database below 100 vectors is insufficient for soft computing methods

# Simple linear regression results (Base circle diameter regressed on growth temperature)

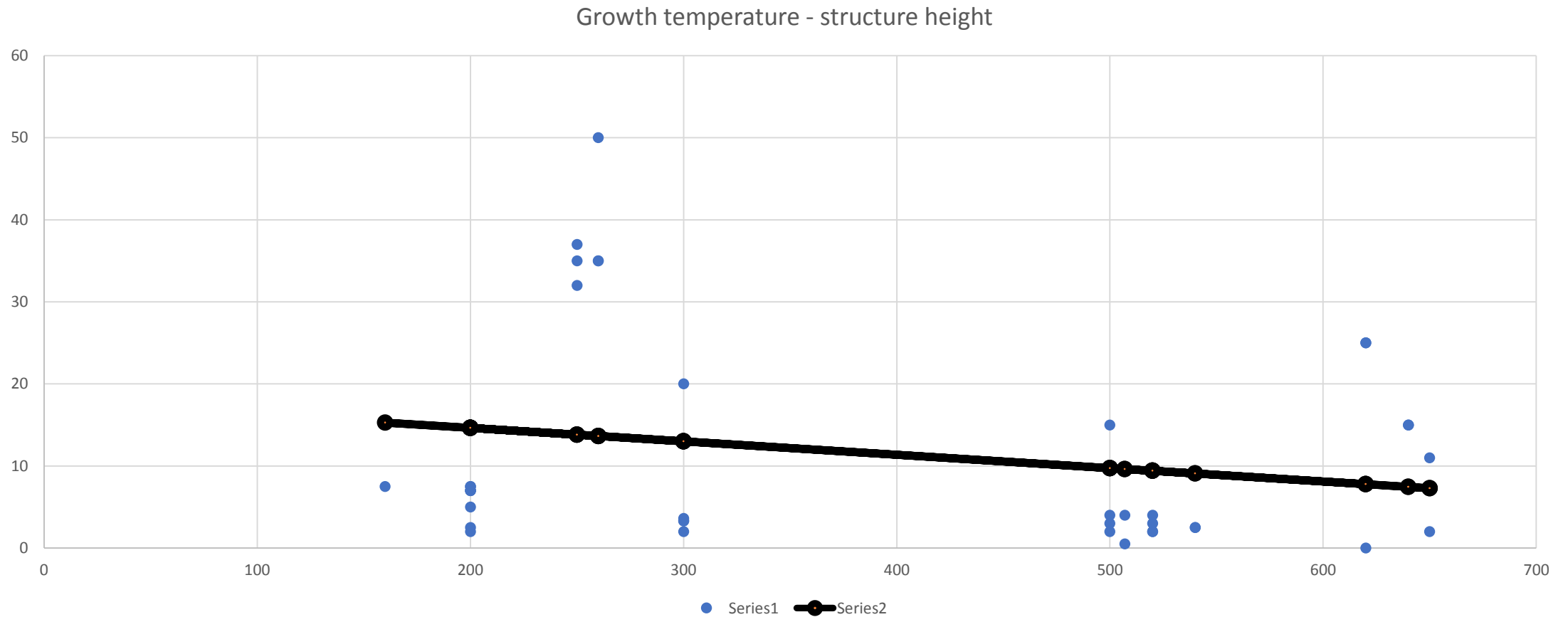




# Simple linear regression results (inner top diameter „ring diameter” regressed on Tg)

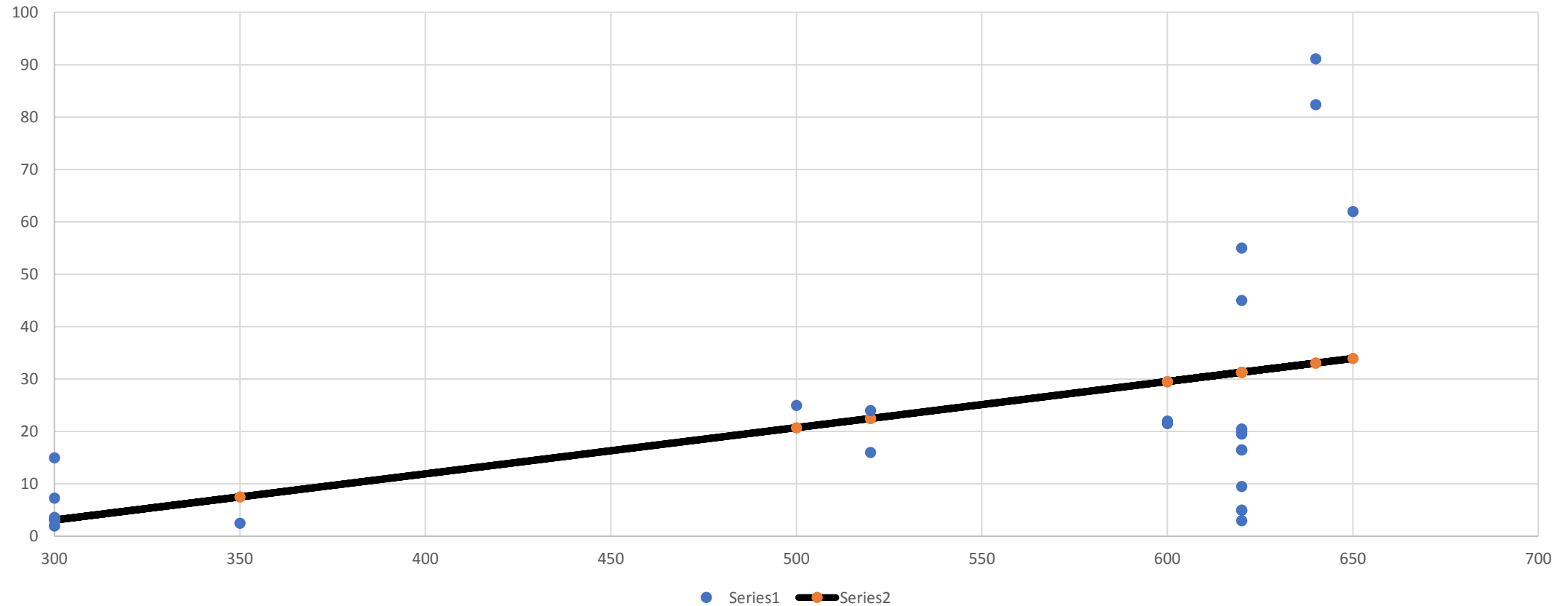


# Simple linear regression results (structure height regressed on growth temperature)



# Simple linear regression results (NH/QR depth regressed on growth temperature)

Growth temperature - nanohole depth



# Explanation to multiple regression results

- Estimate: estimate of coefficient of regression
- SE: standard error of the estimate
- pValue: the null hypothesis of the coefficient being zero can be rejected at  $1 - \text{pValue}$  certainty

# Multiple regression results (base circle diameter regressed on technical parameters)

Var1	Estimate	SE	tStat	pValue
Intercept	46.3155	36.7202	1.2613	0.2143
TGrowth	0.5223	0.0902	5.7884	0.0000
FluxGa	-29.4996	19.0196	-1.5510	0.1286
PressAs	17.4656	10.0012	1.7464	0.0882
AnnealT	3.3025	1.3206	2.5007	0.0165

# Multiple regression results (ring diameter regressed on technical parameters)

Var1	Estimate	SE	tStat	pValue
Intercept	-82.7849	24.4773	-3.3821	0.0016
TGrowth	0.2642	0.0601	4.3936	0.0001
FluxGa	-25.0765	12.6783	-1.9779	0.0547
PressAs	-9.5948	6.6667	-1.4392	0.1577
AnnealT	0.3498	0.8803	0.3974	0.6931

# Multiple regression results (nanostructure height regressed on technical parameters)

Var1	Estimate	SE	tStat	pValue
Intercept	31.29396	5.58941	5.59880	0.00000
TGrowth	0.03788	0.01373	2.75806	0.00865
FluxGa	-3.68565	2.89509	-1.27307	0.21016
PressAs	6.41142	1.52234	4.21156	0.00014
AnnealT	0.81436	0.20102	4.05115	0.00022

# Multiple regression results (QR/NH central depression regressed on technical parameters)

Var1	Estimate	SE	tStat	pValue
Intercept	-20.75379	8.72290	-2.37923	0.02209
TGrowth	0.10693	0.02143	4.98898	0.00001
FluxGa	2.02108	4.51811	0.44733	0.65699
PressAs	1.42182	2.37578	0.59846	0.55282
AnnealT	0.19196	0.31371	0.61190	0.54398



# Conclusion and outlook

- Mathematical description of the relationship between technological and geometrical parameters
- Support of the technology of the droplet epitaxial nano-structure preparation

Thank you your attention